

In the Specification

Amend the title as follows:

Magnetoresistive Memory Devices And Assemblies; ~~And Methods Of Storing And Retrieving Information~~

Amend paragraph [0008] as follows:

[0008] In one aspect, the invention encompasses a magnetoresistive memory device assembly. The assembly includes an array of individual magnetoresistive memory devices. The devices include memory bits. The individual memory bits comprise a stack of a pair of magnetic layers separated by a non-magnetic layer. A first conductive line is proximate the stack and utilized for reading information from the memory bit. A second conductive line is spaced from the stack by a greater distance than the first conductive line and is configured for utilization in writing information to the memory bit. The first conductive line extends across a first set of several of the individual magnetoresistive memory devices of the array, and the ~~common~~ second conductive line also extends across the first set of the individual magnetoresistive memory devices of the array. A first transistor is electrically connected with the first conductive line and accordingly electrically connected with the first set of individual magnetoresistive memory devices. Additionally, a second transistor is electrically connected with the second conductive line, and accordingly electrically connected with the first set of the individual magnetoresistive memory devices of the array.

Amend paragraph [0014] as follows:

[0014] A ~~first~~ An electrically conductive line 14 is supported by substrate 12, an electrically insulative layer 16 is over line 14, and a ~~second~~ an electrically conductive line 18 is over electrically insulative layer 16. In the discussion and claims that follow, conductive line 18 can be referred to as a first conductive line, and conductive line 14 can be referred to as a second conductive line. Conductive lines 14 and 18 can comprise any of numerous conductive materials, including, for example, metals, metal compositions, and conductively-doped semiconductive materials. Insulative layer 16 can comprise any of numerous electrically insulative materials, including, for example, silicon dioxide, silicon nitride, and/or so-called low-k materials.

Amend paragraph [0016] as follows:

[0016] A third conductive line 28 is provided over the memory bit, and extends in an orthogonal orientation relative to first and second conductive lines ~~14 18~~ and ~~18 14~~. Accordingly, third conductive line 28 extends into and out of the page in the shown orientation of construction 10. Conductive line 28 can comprise any of numerous conductive materials, including, for example, metals and metal compositions. Conductive line 28 physical contacts magnetic layer 22 in the shown embodiment.

Amend the "Abstract" on page 29 as follows:

The invention ~~encompasses~~ includes a magnetoresistive memory device. ~~The device includes a memory bit which comprises a~~ having a memory bit stack. ~~The stack having~~ includes a first magnetic layer, a second magnetic layer, and a non-magnetic layer between the first and second magnetic layers. A first conductive line is proximate the stack and configured for utilization in reading information from the memory bit. The first conductive line is ohmically connecting with either the first or second magnetic layer. A second conductive line is spaced from the stack by ~~a greater distance than the first conductive line is spaced from the stack~~ a sufficient distance that the second conductive line is not ohmically connected to the stack, and is configured for utilization in writing information to the memory bit. ~~The invention also encompasses methods of storing and retrieving information in a cross-point array architecture.~~